VS-ST230C Series

Vishay Semiconductors



Phase Control Thyristors (Hockey PUK Version), 410 A



A-PUK (TO-200AB)

PRIMARY CHARACTERISTICS							
I _{T(AV)}	410 A						
V _{DRM} /V _{RRM}	400 V, 800 V, 1200 V, 1400 V, 1600 V, 1800 V, 2000 V						
V _{TM}	1.69 V						
I _{GT}	90 mA						
TJ	-40 °C to +125 °C						
Package	A-PUK (TO-200AB)						
Circuit configuration	Single SCR						

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-PUK (TO-200AB)
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	METER TEST CONDITIONS VALUES								
I		410	А						
I _{T(AV)}	T _{hs}	55	°C						
I		780	А						
IT(RMS)	T _{hs}	25	°C						
	50 Hz	5700	٨						
ITSM	60 Hz	5970	A						
l ² t	50 Hz	163	kA ² s						
1-t	60 Hz	149	KA∸S						
V _{DRM} /V _{RRM}		400 to 2000	V						
t _q	Typical	100	μs						
TJ		-40 to +125	°C						

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} , MAXIMUM AT T _J = T _J MAXIMUM MA					
	04	400	500						
	08	800	900						
	12	1200	1300						
VS-ST230CC	14	1400	1500	30					
	16	1600	1700						
	18	1800	1900						
	20	2000	2100						

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COMPLIANT

VS-ST230C Series



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ABSOLUTE MAXIMUM RATING	5						
PARAMETER	SYMBOL		TEST CONDITIONS				
Maximum average on-state current	L	180° condu	ction, half sine	wave	410 (165)	А	
at heatsink temperature	I _{T(AV)}	double side	e (single side) co	oled	55 (85)	°C	
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	780		
		t = 10 ms	No voltage		5700		
Maximum peak, one-cycle	L	t = 8.3 ms	reapplied		5970	А	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		4800	kA ² s	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	5000		
	l ² t	t = 10 ms	No voltage reapplied	initial T _J = T _J maximum	163		
Maximum I ² t for fusing		t = 8.3 ms			148		
Maximum - tior fusing		t = 10 ms	100 % V _{RBM}		115		
		t = 8.3 ms	reapplied		105		
Maximum I ² √t for fusing	l²√t	t = 0.1 to 10) ms, no voltage	e reapplied	1630	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.92	v	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$				
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.88	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			0.81	1115.2	
Maximum on-state voltage	V _{TM}	I _{pk} = 880 A,	1.69	V			
Maximum holding current	Ι _Η	T _ 05 °C	anada ayarki 1	2.V. registive load	600	m۸	
Maximum (typical) latching current	١L	1j=25 C,	anoue supply 1	2 V resistive load	1000 (300)	mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \leq 1~\mu s$ T_J = T_J maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0	
Typical turn-off time	tq	I_{TM} = 300 A, T_J = T_J maximum, dl/dt = 20 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA



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TRIGGERING							
PARAMETER	SYMBOL	те	TEST CONDITIONS			UNITS	
FANAMETEN	STNIBOL	16	STEENDITIONS	TYP.	MAX.		
Maximum peak gate power	P _{GM}	$T_J = T_J maximum$	t _p ≤ 5 ms	10	0.0	W	
Maximum average gate power	P _{G(AV)}	$T_J = T_J maximum$	f = 50 Hz, d% = 50	2	.0	vv	
Maximum peak positive gate current	I _{GM}	$T_J = T_J maximum$	t _p ≤ 5 ms	3	.0	А	
Maximum peak positive gate voltage	+ V _{GM}		t < 5 mg	2	0	V	
Maximum peak negative gate voltage	- V _{GM}	ij = ij maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms			v	
		T _J = - 40 °C		180	-		
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger/	90	150	mA	
		T _J = 125 °C	current/voltage are the lowest	40	-		
		$T_J = -40 \ ^{\circ}C$ value which will trigger all units		2.9	-		
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	12 V anode to cathode applied	1.8	3.0	V	
		T _J = 125 °C		1.2	-		
DC gate current not to trigger	I _{GD}		Maximum gate current/voltage	1	0	mA	
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V	

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum operating temperature range	TJ		-40 to 125	°C				
Maximum storage temperature range	T _{Stg}		-40 to 150					
Maximum thermal resistance,	Р	DC operation single side cooled	0.17					
junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.08	κ/w				
Maximum thermal resistance,	D	DC operation single side cooled	0.033	r\/ vv				
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.017					
Mounting force, ± 10 %			4900 (500)	N (kg)				
Approximate weight			50	g				
Case style		See dimensions - link at the end of datasheet	A-PUK (TO-2	200AB)				

$\Delta \mathbf{R}_{\text{thJC}}$ CONDUCTION							
	SINUSOIDAL	CONDUCTION	RECTANGULAR	R CONDUCTION	TEST CONDITIONS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE DOUBLE SIDE		TEST CONDITIONS	UNITS	
180°	0.015	0.017	0.011	0.011			
120°	0.018	0.019	0.019	0.019			
90°	0.024	0.024	0.026	0.026	$T_J = T_J maximum$	K/W	
60°	0.035	0.035	0.036	0.036			
30°	0.060	0.060	0.060	0.061			

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



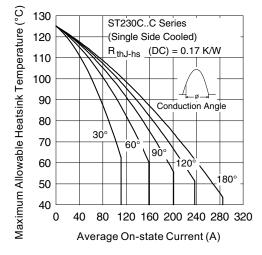


Fig. 1 - Current Ratings Characteristics

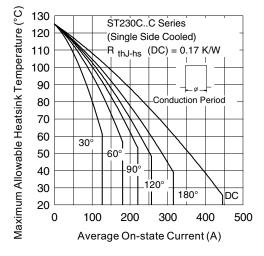
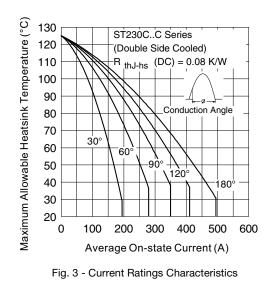


Fig. 2 - Current Ratings Characteristics





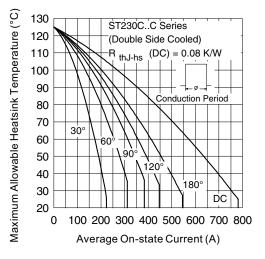


Fig. 4 - Current Ratings Characteristics

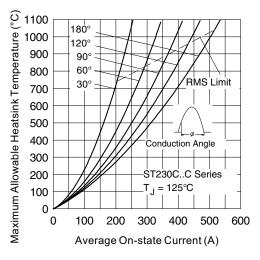


Fig. 5 - On-State Power Loss Characteristics

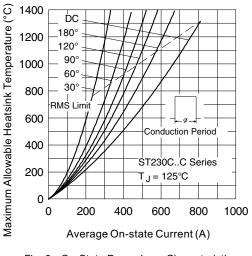


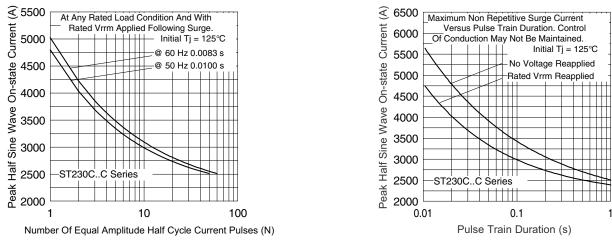
Fig. 6 - On-State Power Loss Characteristics

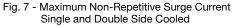
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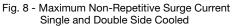
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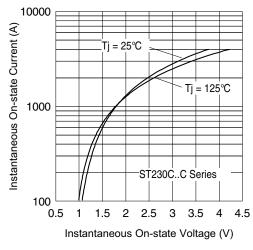
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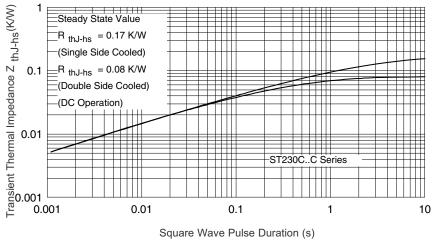


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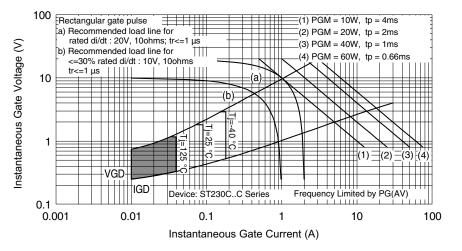


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

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Device code	vs-	ST	23	0	С	20	С	1	-	
	1	2	3	4	5	6	7	8	9	
 Vishay Semiconductors product Thyristor Essential part number 0 = converter grade C = ceramic PUK Voltage code x 100 = V_{RRM} (see Voltage Ratings table) C = PUK case A-PUK (TO-200AB) 0 = eyelet terminals (gate and auxiliary cathode unsoldered) 									ed leads) red leads)	
	9 -	2 = 3 =	eyelet t fast-on	erminals terminal dt: • Nor	s (gate a s (gate a ls (gate ne = 500 1000 V	and auxi and aux) V/µs (s	liary ca iliary ca standar	thode s athode s d select	oldered soldered	leads)

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95074



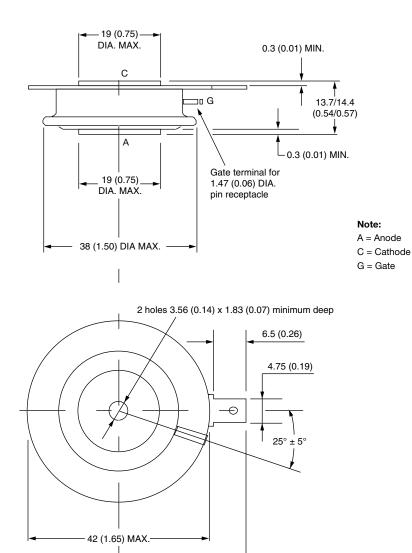


A-PUK (TO-200AB)

DIMENSIONS in millimeters (inches)

Anode to gate

Creepage distance: 7.62 (0.30) minimum Strike distance: 7.12 (0.28) minimum



◄ 28 (1.10) →

Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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